THE ANNEALING OF DEFECT CLUSTERS IN CZOCHRALSKI-GROWN Si AND Si⟨Ge⟩ SAMPLES

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S u m m a r y

Czochralski-grown n-type silicon (Cz-Si) samples doped by germanium ($N_{\mathrm{Ge}} = 2 \times 10^{20}$ cm^{-3}) and without that were investigated after the irradiation by fast neutrons. The isothermal annealing of n-Si⟨Ge⟩ after the irradiation with a fluence of 1.4×10^{14} neutr./cm^2 was studied for three temperatures. It is shown that the annealing of defect clusters is caused by the annihilation of vacancy-type defects in the clusters with interstitial defects. The annealing of neutron-irradiated n-type Cz-Si by gamma irradiation was observed.